

Electronic Devices and Circuit Theory

Boylestad

DC Biasing - BJTs

Chapter 4

Ch.4 Summary

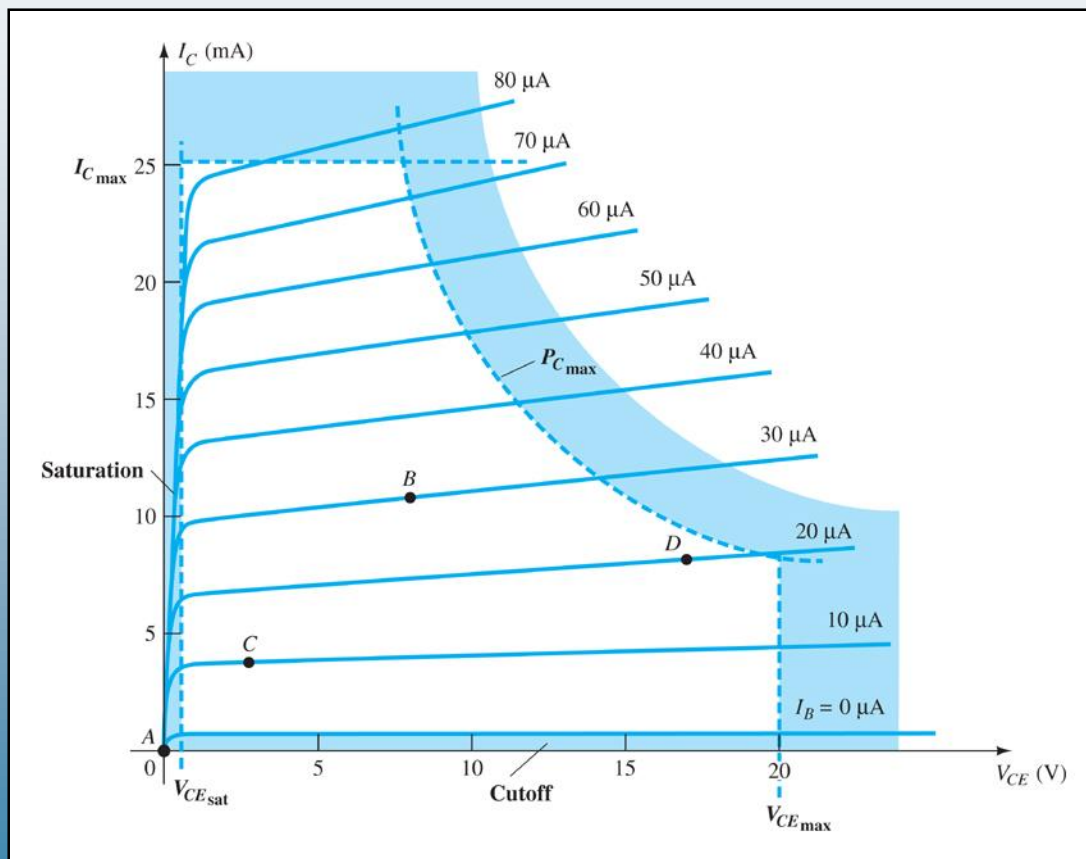
Biasing

Biasing: Applying DC voltages to a transistor in order to turn it on so that it can amplify AC signals.

Ch.4 Summary

Operating Point

The DC input establishes an operating or *quiescent point* called the **Q-point**.



The Three Operating Regions

Active or Linear Region Operation

- Base–Emitter junction is forward biased
- Base–Collector junction is reverse biased

Cutoff Region Operation

- Base–Emitter junction is reverse biased

Saturation Region Operation

- Base–Emitter junction is forward biased
- Base–Collector junction is forward biased

Ch.4 Summary

DC Biasing Circuits

Fixed-bias circuit

Emitter-stabilized bias circuit

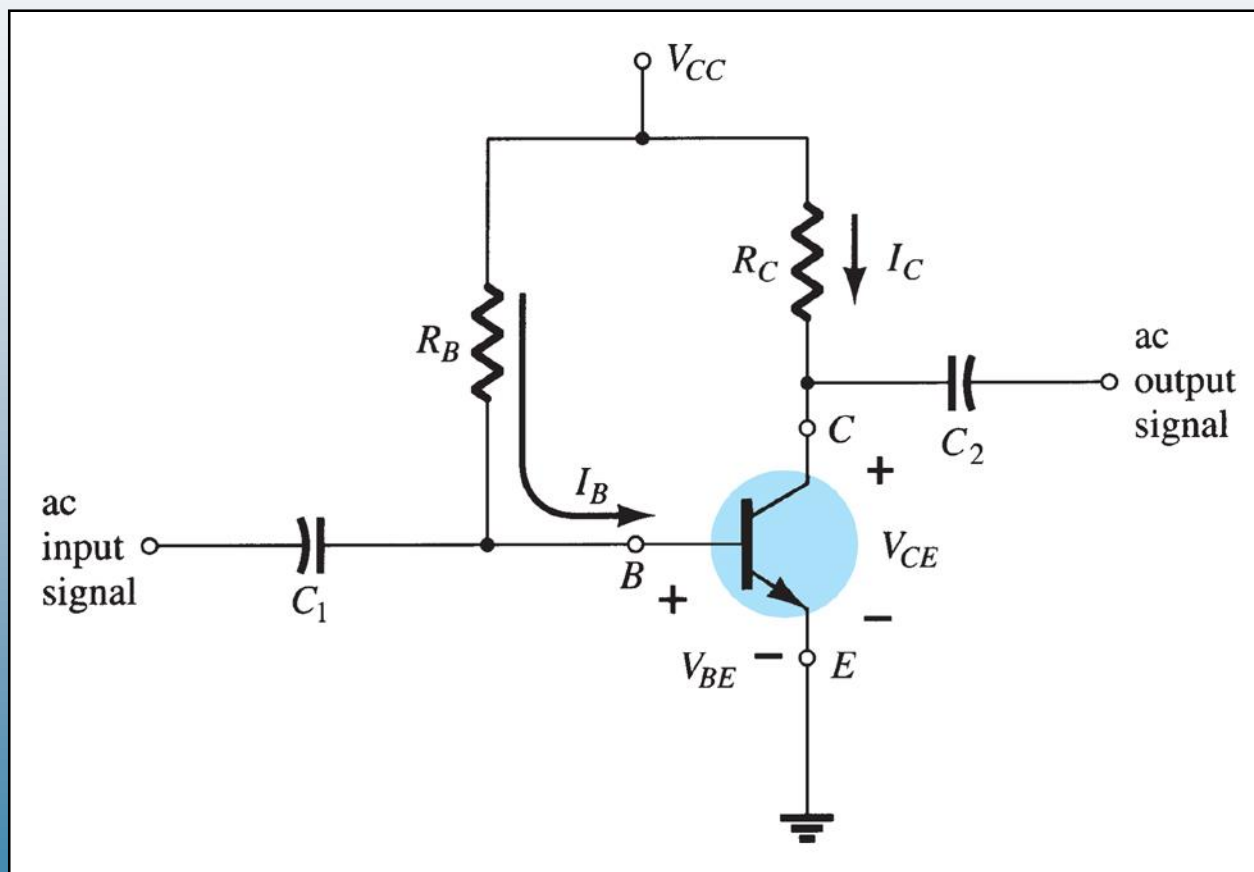
Collector-emitter loop

Voltage divider bias circuit

DC bias with voltage feedback

Ch.4 Summary

Fixed Bias



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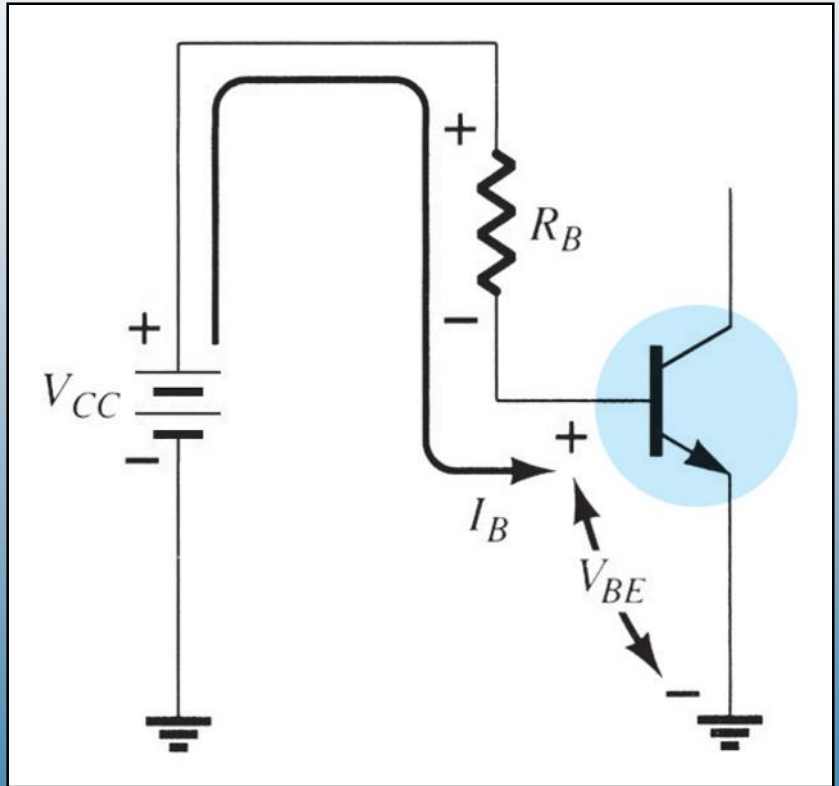
The Base-Emitter Loop

From Kirchhoff's voltage law:

$$+V_{CC} - I_B R_B - V_{BE} = 0$$

Solving for base current:

$$I_B = \frac{V_{CC} - V_{BE}}{R_B}$$



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Collector-Emitter Loop

Collector current:

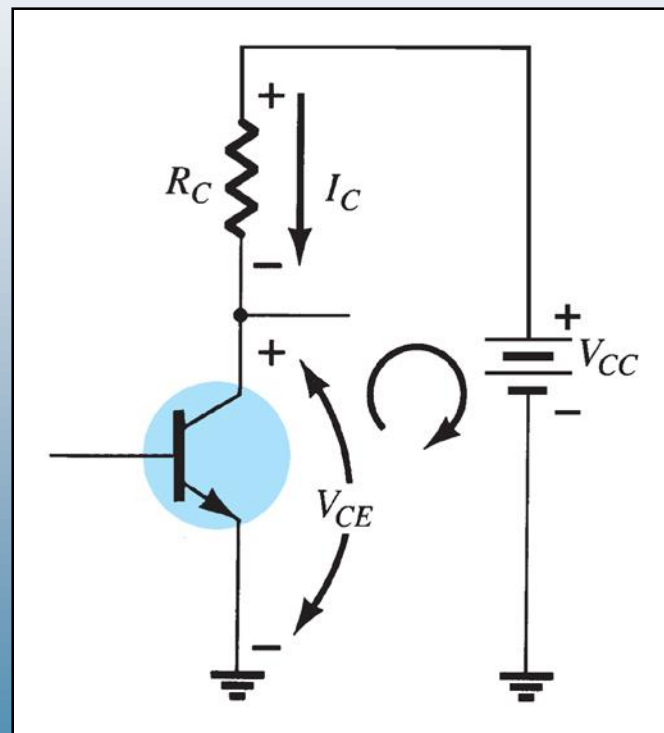
$$I_C = \beta I_B$$

From Kirchhoff's voltage law:

$$V_{CE} = V_{CC} - I_C R_C$$

$$V_{CE} = V_C - V_E$$

$$V_{BE} = V_B - V_E$$



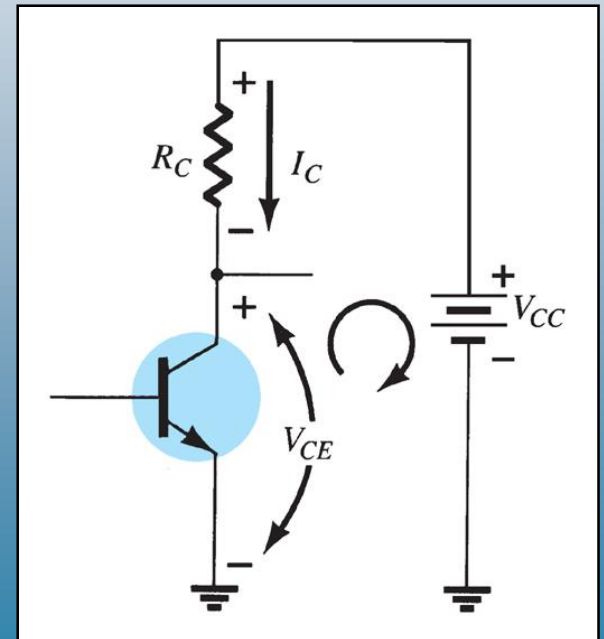
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Saturation

When the transistor is operating in **saturation**, current through the transistor is at its *maximum* possible value.

$$I_{Csat} = \frac{V_{CC}}{R_C}$$

$$V_{CE} \cong 0 \text{ V}$$



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Load Line Analysis

The load line end points are:

$I_{C\text{sat}}$

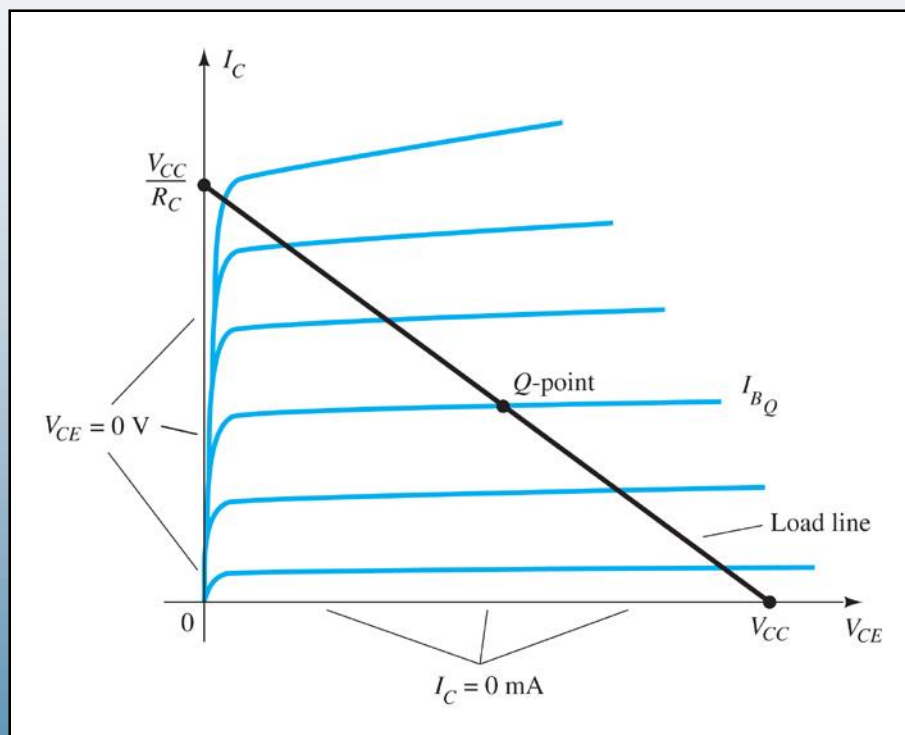
$$V_{CE} = 0 \text{ V}$$

$$I_C = V_{CC} / R_C$$

$V_{CE\text{cutoff}}$

$$I_C = 0 \text{ mA}$$

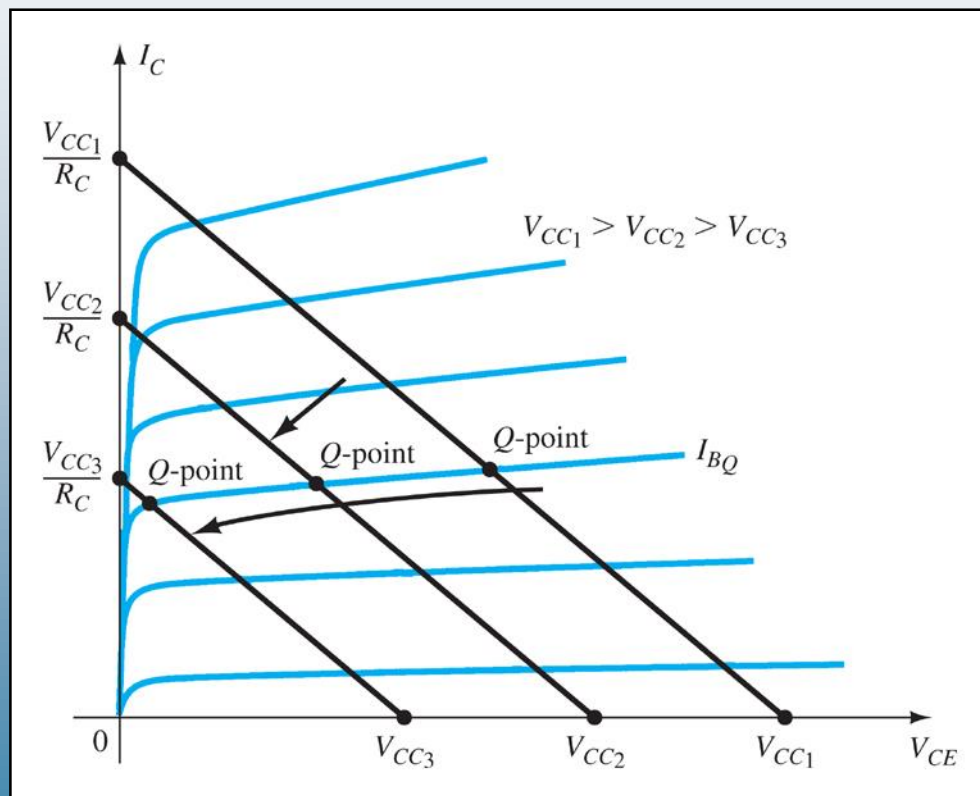
$$V_{CE} = V_{CC}$$



The Q-point is the operating point where the value of R_B sets the value of I_B that controls the values of V_{CE} and I_C .

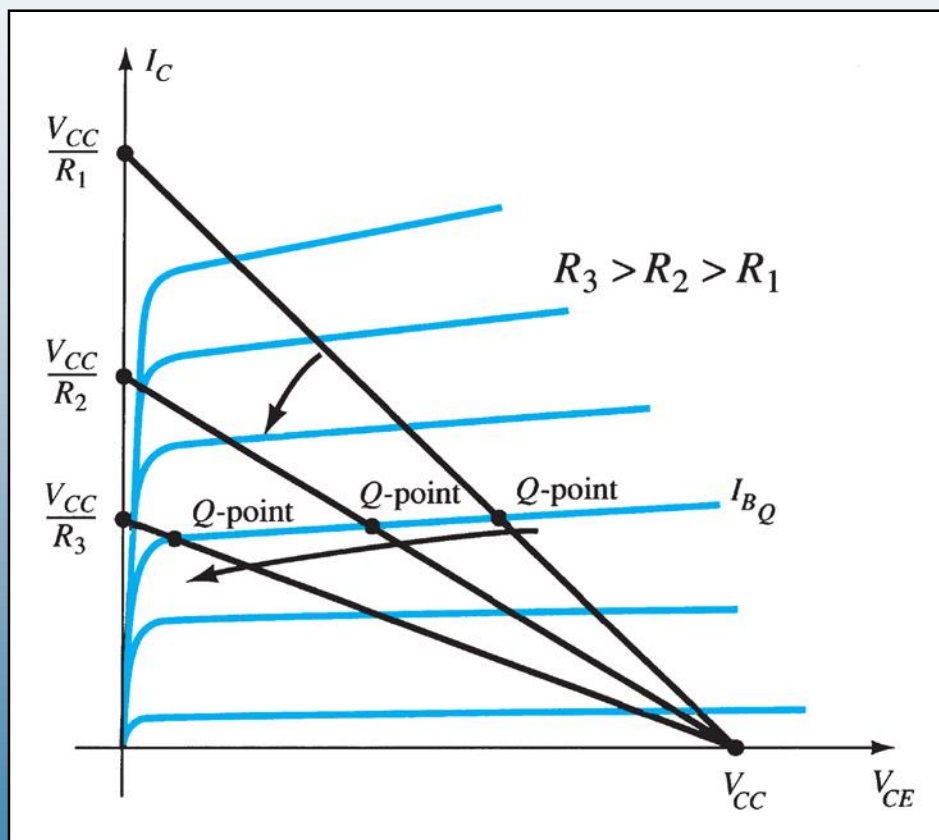
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The Effect of V_{CC} on the Q-Point



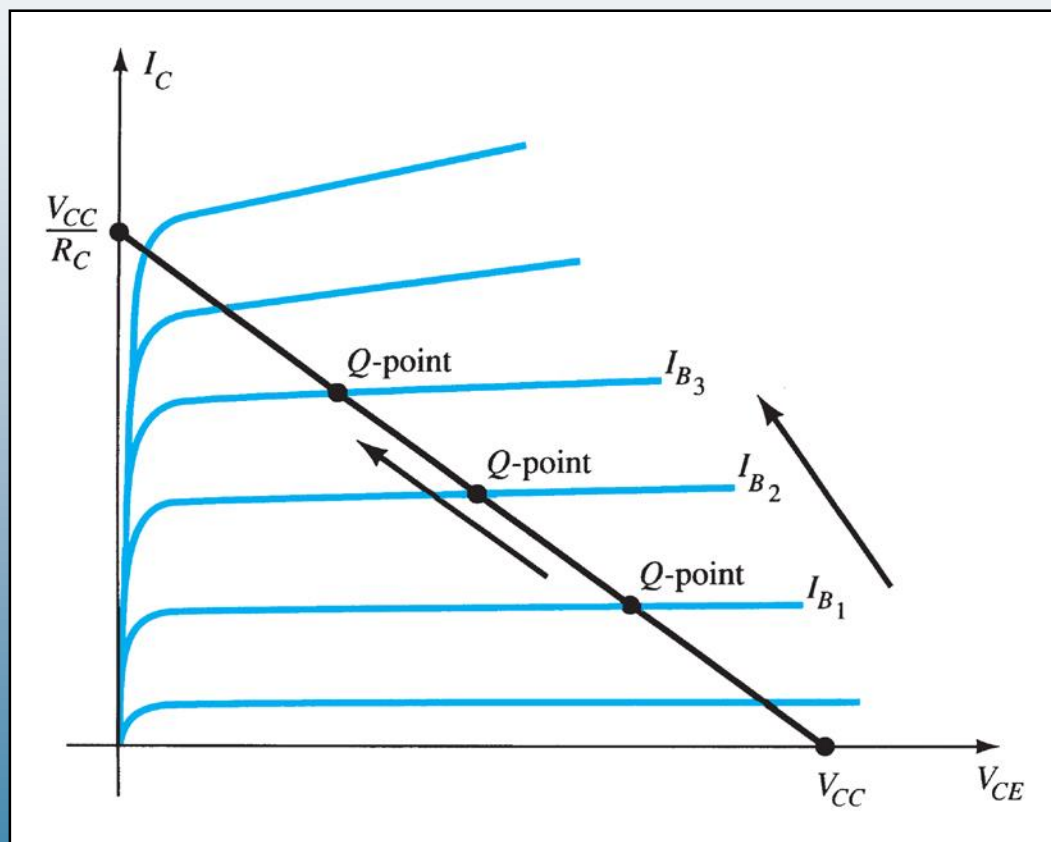
Ch.4 Summary

The Effect of R_C on the Q-Point



Ch.4 Summary

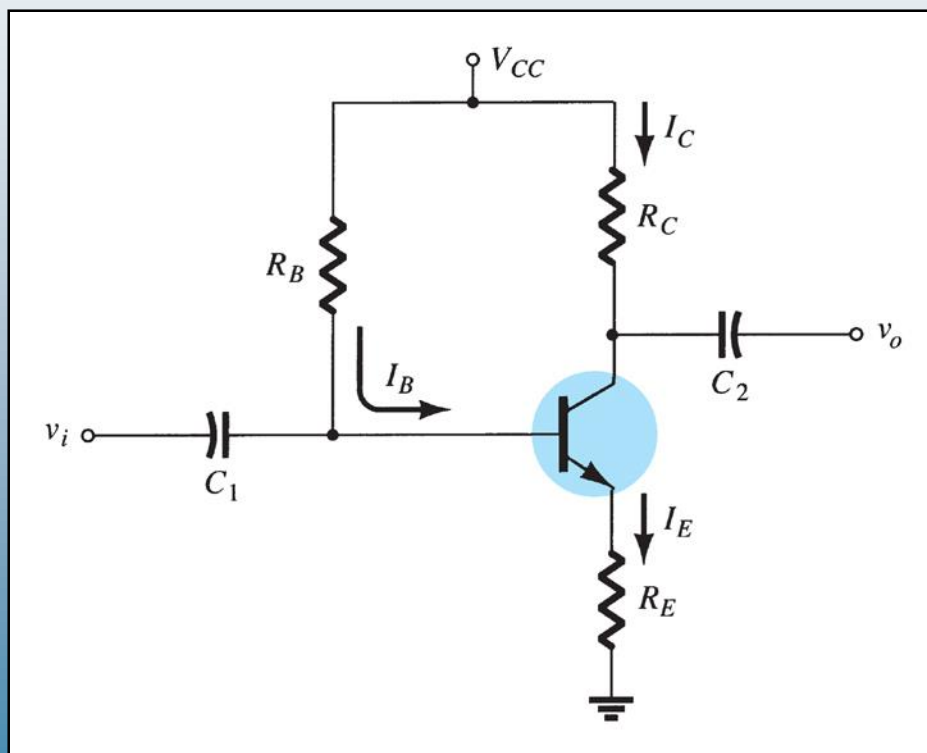
The Effect of I_B on the Q-Point



Ch.4 Summary

Emitter-Stabilized Bias Circuit

Adding a resistor (R_E) to the emitter circuit stabilizes the bias circuit.



Ch.4 Summary

Base-Emitter Loop

From Kirchhoff's voltage law:

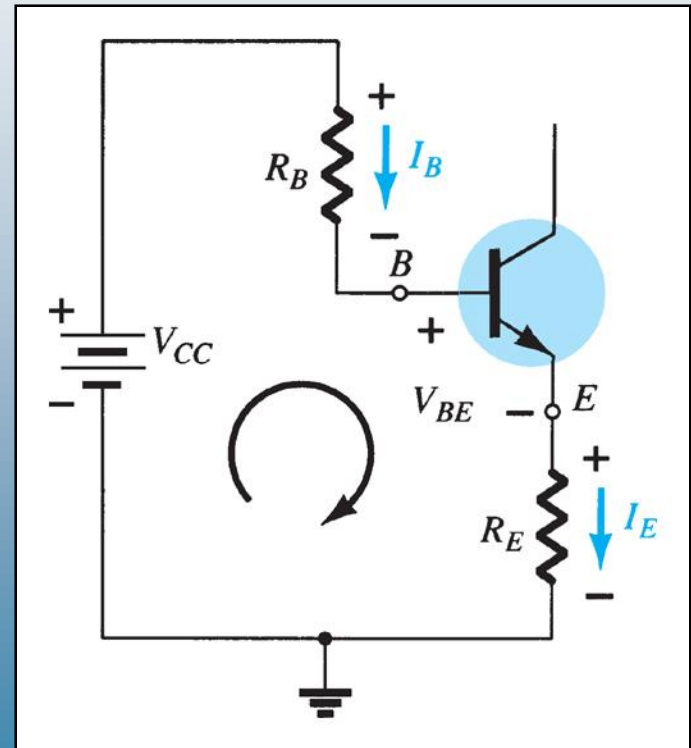
$$+V_{CC} - I_B R_B - V_{BE} - I_E R_E = 0$$

Since $I_E = (\beta + 1)I_B$:

$$V_{CC} - I_B R_B - (\beta + 1)I_B R_E = 0$$

Solving for I_B :

$$I_B = \frac{V_{CC} - V_{BE}}{R_B + (\beta + 1)R_E}$$



Ch.4 Summary

Collector-Emitter Loop

From Kirchhoff's voltage law:

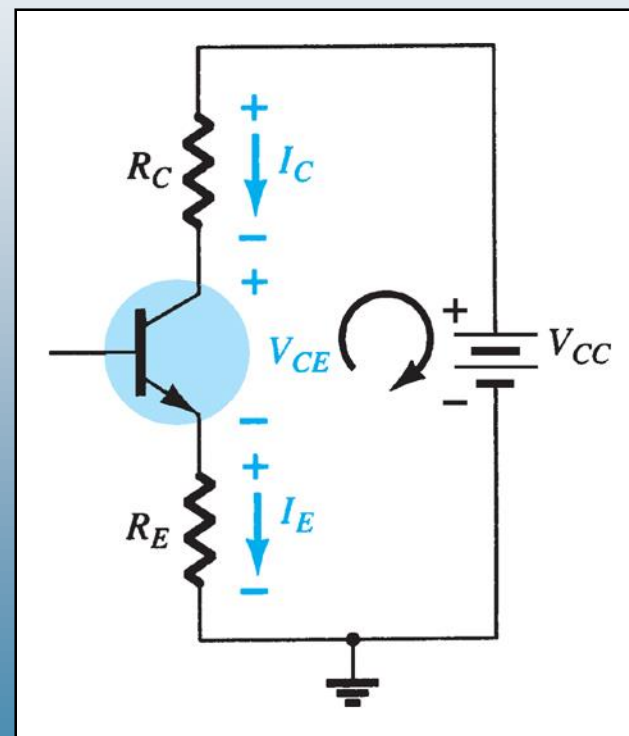
$$I_E R_E + V_{CE} + I_C R_C - V_{CC} = 0$$

Since $I_E \cong I_C$:

$$V_{CE} = V_{CC} - I_C(R_C + R_E)$$

Also:

$$\begin{aligned} V_E &= I_E R_E \\ V_C &= V_{CE} + V_E = V_{CC} - I_C R_C \\ V_B &= V_{BE} + V_E \end{aligned}$$



Ch.4 Summary

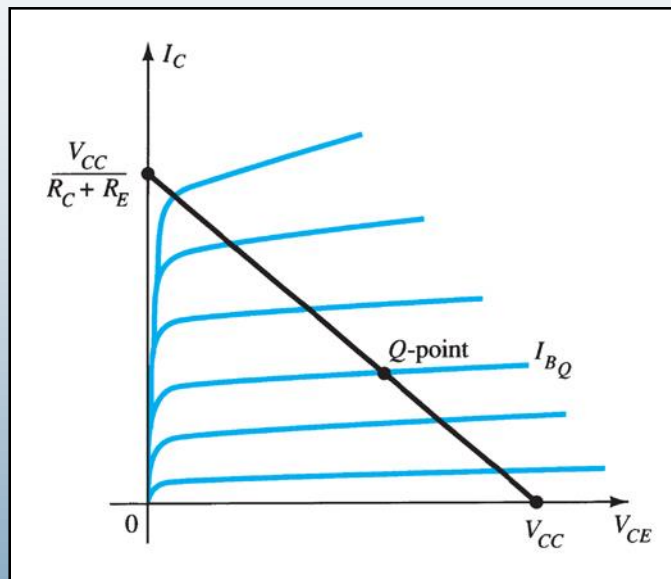
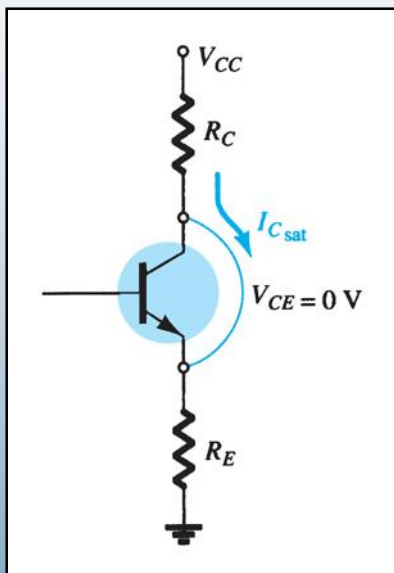
Improved Biased Stability

Stability refers to a condition in which the currents and voltages remain fairly constant over a wide range of temperatures and transistor Beta (β) values.

Adding R_E to the emitter improves the stability of a transistor.

Ch.4 Summary

Saturation Level



The endpoints can be determined from the load line.

$V_{CE\text{ cutoff}}$:

$$I_C = 0\text{ mA}$$

$$V_{CE} = V_{CC}$$

$I_{C\text{ sat}}$:

$$V_{CE} = 0\text{ V}$$

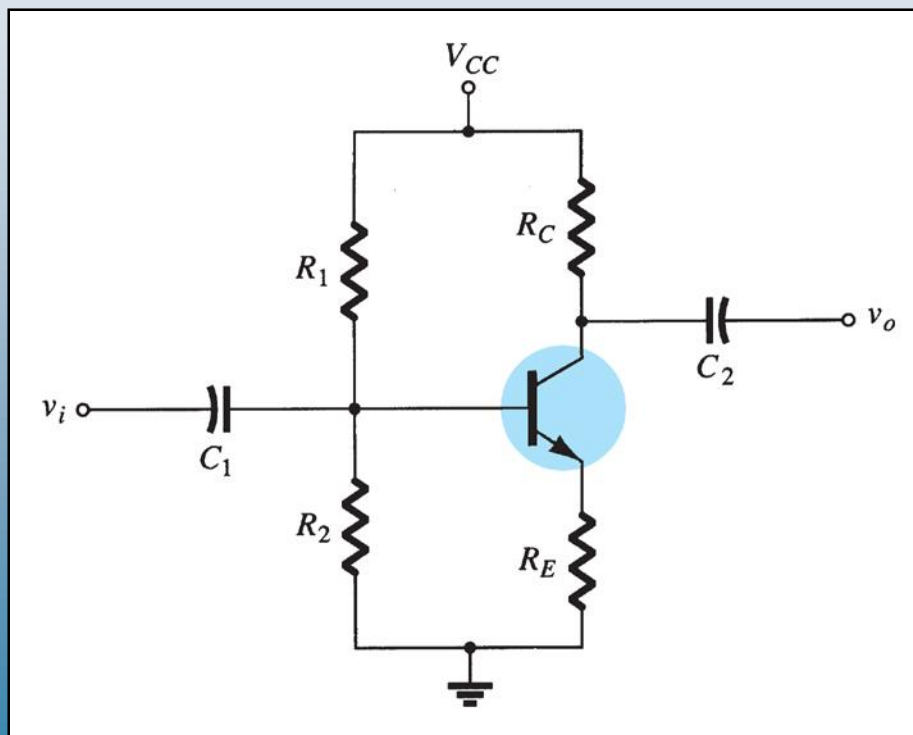
$$I_C = \frac{V_{CC}}{R_C + R_E}$$

Ch.4 Summary

Voltage Divider Bias

This is a very stable bias circuit.

The currents and voltages are nearly independent of any variations in β .



Ch.4 Summary

Approximate Analysis

Where $I_B \ll I_1$ and $I_1 \cong I_2$:

$$V_B = \frac{R_2 V_{CC}}{R_1 + R_2}$$

Where $\beta R_E > 10R_2$:

0.7 $\rightarrow$

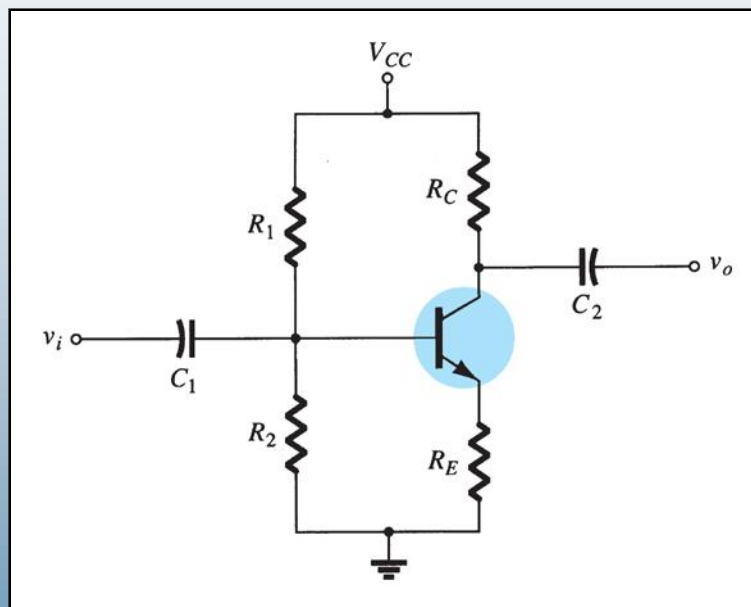
$$V_{BE} = V_B - V_E$$
$$I_E = \frac{V_E}{R_E}$$

From Kirchhoff's voltage law:

$$V_{CE} = V_{CC} - I_C R_C - I_E R_E$$

$$I_E \cong I_C$$

$$V_{CE} = V_{CC} - I_C (R_C + R_E)$$



Ch.4 Summary

Voltage Divider Bias Analysis

Transistor Saturation Level

$$I_{Csat} = I_{Cmax} = \frac{V_{CC}}{R_C + R_E}$$

Load Line Analysis

Cutoff:

$$V_{CE} = V_{CC}$$
$$I_C = 0 \text{ mA}$$

Saturation:

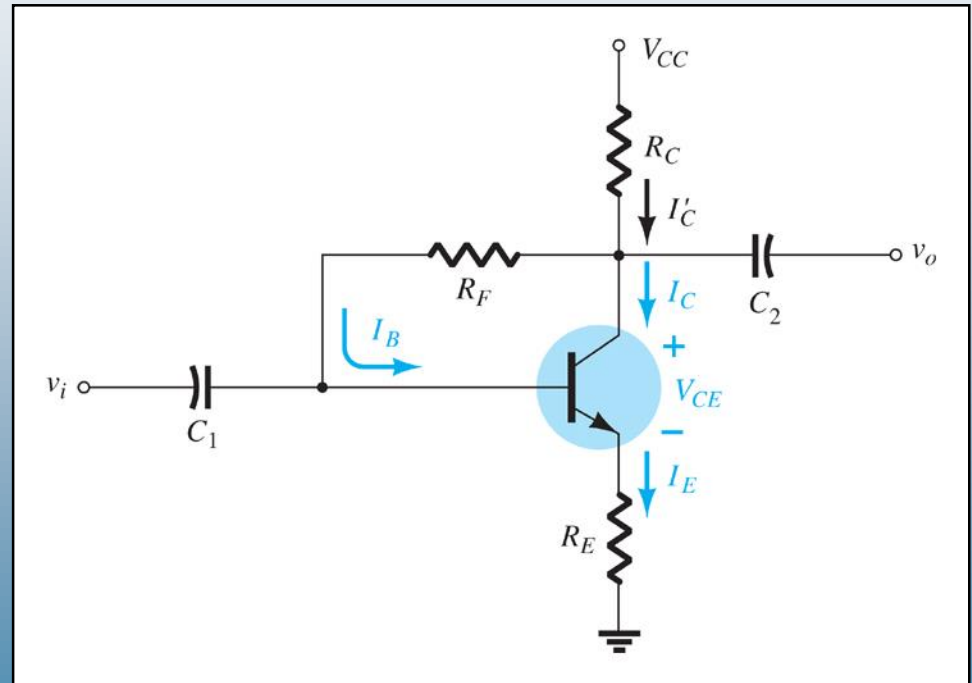
$$I_C = \frac{V_{CC}}{R_C + R_E}$$
$$V_{CE} = 0 \text{ V}$$

Ch.4 Summary

DC Bias With Voltage Feedback

Another way to improve the stability of a bias circuit is to add a feedback path from collector to base.

In this bias circuit the Q-point is only slightly dependent on the transistor beta, β .



Ch.4 Summary

Base-Emitter Loop

From Kirchhoff's voltage law:

$$V_{CC} - I'_C R_C - I_B R_F - V_{BE} - I_E R_E = 0$$

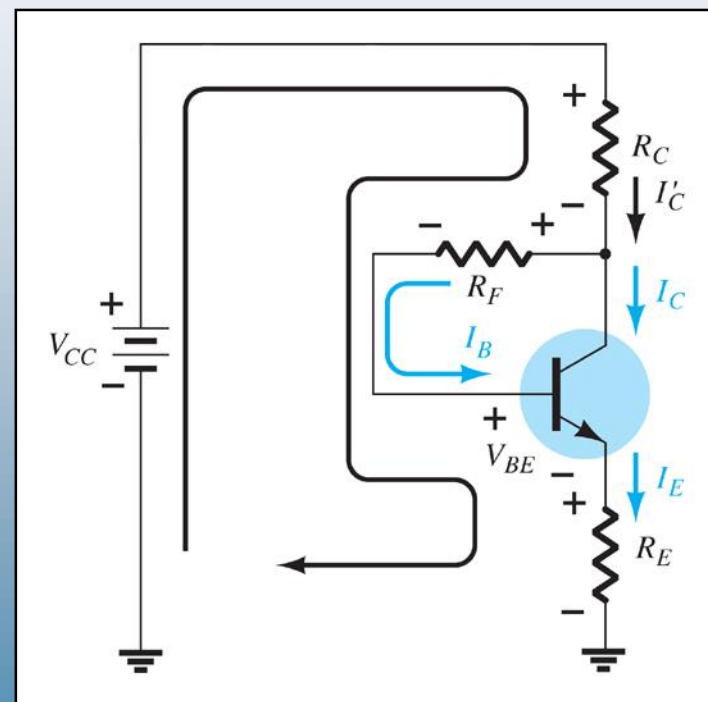
Where $I_B \ll I_C$: $I'_C = I_C + I_B \cong I_C$

Knowing $I_C = \beta I_B$ and $I_E \cong I_C$, the loop equation becomes:

$$V_{CC} - \beta I_B R_C - I_B R_F - V_{BE} - \beta I_B R_E = 0$$

Solving for I_B :

$$I_B = \frac{V_{CC} - V_{BE}}{R_F + \beta(R_C + R_E)}$$



Ch.4 Summary

Collector-Emitter Loop

Applying Kirchhoff's voltage law:

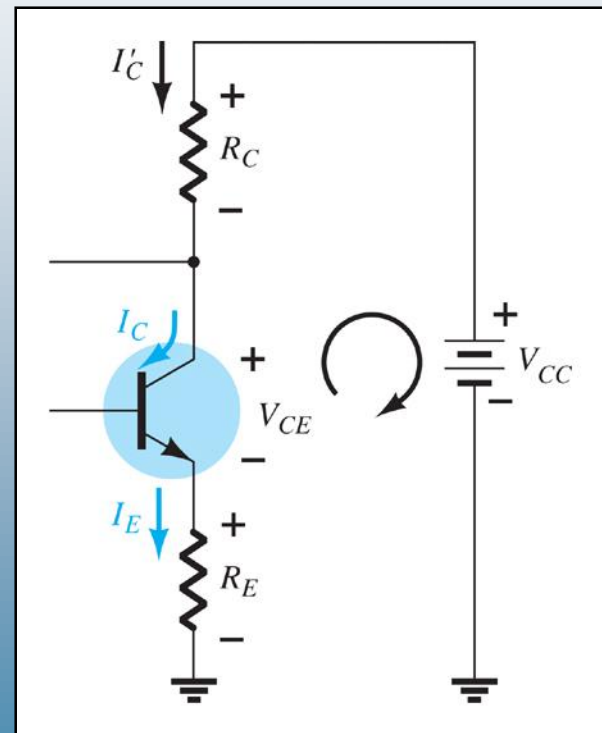
$$R_E I_E + V_{CE} + I'_C R_C - V_{CC} = 0$$

Since $I'_C \cong I_C$ and $I_E \cong I_C$

$$I_C(R_C + R_E) + V_{CE} - V_{CC} = 0$$

Solving for V_{CE} :

$$V_{CE} = V_{CC} - I_C(R_C + R_E)$$



Ch.4 Summary

Base-Emitter Bias Analysis

Transistor Saturation Level

$$I_{Csat} = I_{Cmax} = \frac{V_{CC}}{R_C + R_E}$$

Load Line Analysis

Cutoff

$$\begin{aligned} V_{CE} &= V_{CC} \\ I_C &= 0 \text{ mA} \end{aligned}$$

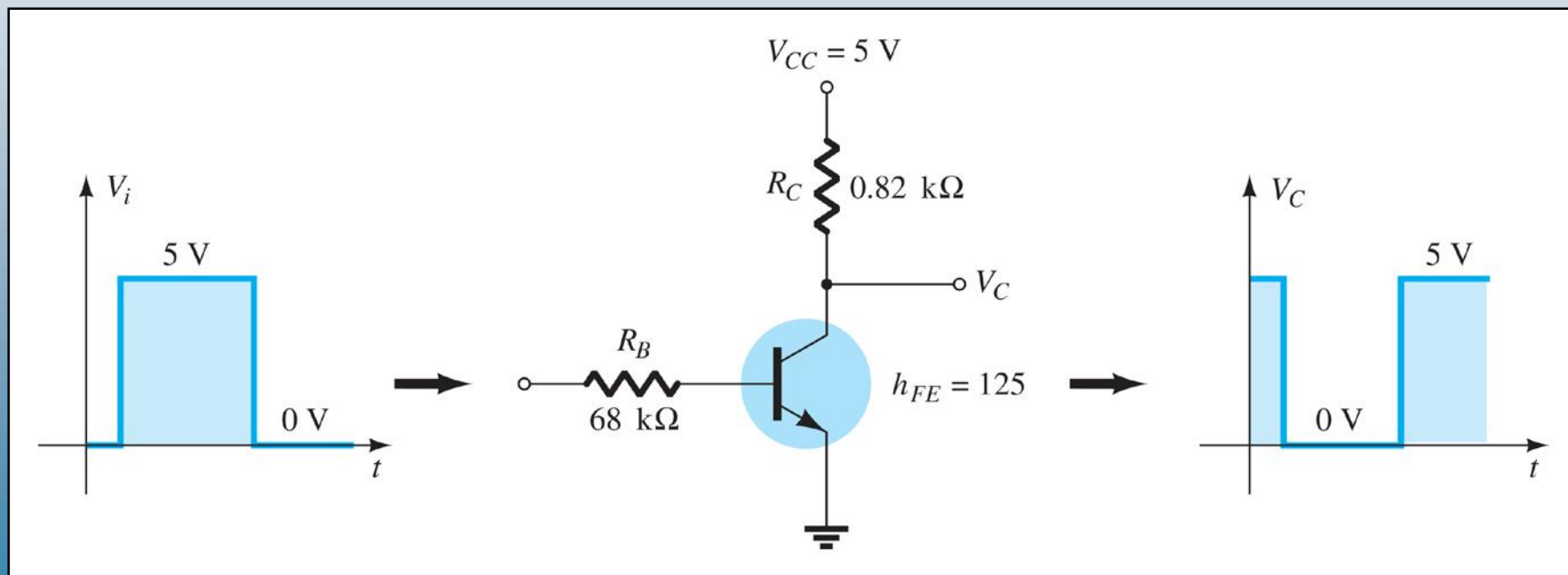
Saturation

$$\begin{aligned} I_C &= \frac{V_{CC}}{R_C + R_E} \\ V_{CE} &= 0 \text{ V} \end{aligned}$$

Ch.4 Summary

Transistor Switching Networks

Transistors with only the DC source applied can be used as electronic switches.



Ch.4 Summary

Switching Circuit Calculations

Saturation current:

$$I_{Csat} = \frac{V_{CC}}{R_C}$$

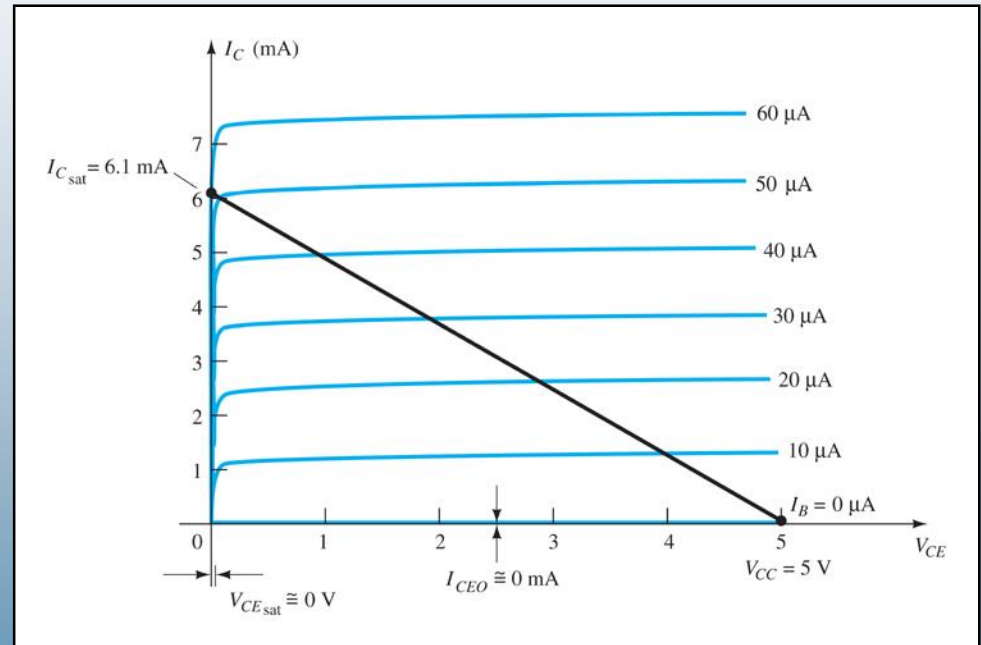
To ensure saturation:

$$I_B > \frac{I_{Csat}}{\beta_{dc}}$$

Emitter-collector
resistance at
saturation and cutoff:

$$R_{sat} = \frac{V_{CEsat}}{I_{Csat}}$$

$$R_{cutoff} = \frac{V_{CC}}{I_{CEO}}$$



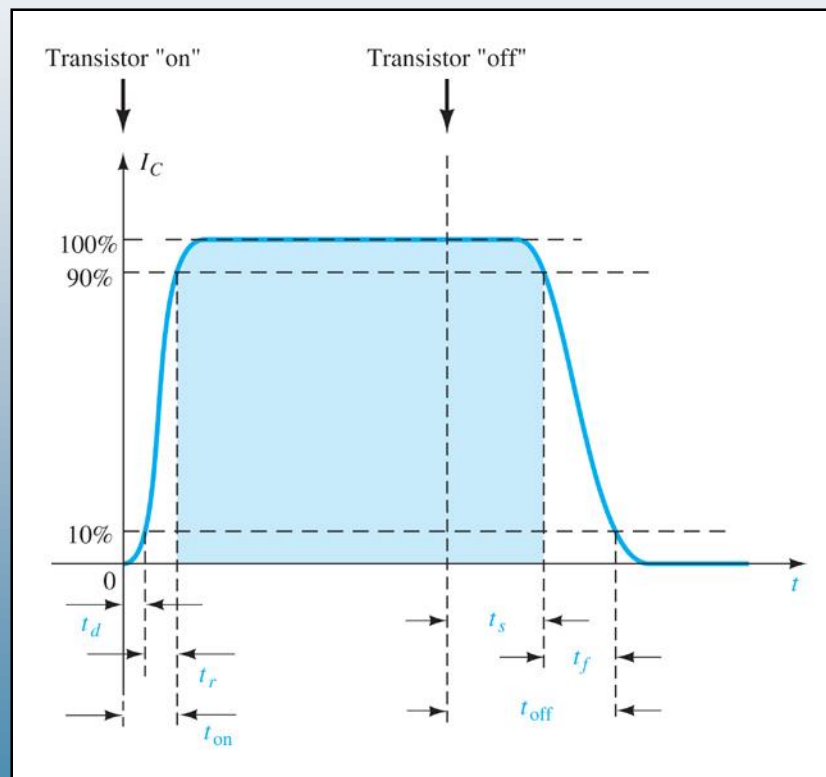
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Switching Time

Transistor switching times:

$$t_{on} = t_r + t_d$$

$$t_{off} = t_s + t_f$$



Ch.4 Summary

Troubleshooting Hints

Approximate voltages

$V_{BE} \cong 0.7 \text{ V}$ for silicon transistors

$V_{CE} \cong 25\% \text{ to } 75\% \text{ of } V_{CC}$

Test for opens and shorts with an ohmmeter.

Test the solder joints.

Test the transistor with a transistor tester or a curve tracer.

Note that the load or the next stage affects the transistor operation.

Ch.4 Summary

PNP Transistors

The analysis for *pnp* transistor biasing circuits is the same as that for *npn* transistor circuits. The only difference is that the currents are flowing in the opposite direction.